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APR 22 2003
TECHNOLOGY CENTER 2800

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q56799

Masami HATORI

Appln. No.: 09/533,678

Group Art Unit: 2828

Confirmation No.: 1082

Examiner: Tuan M. Nguyen

Filed: March 23, 2000

For: SEMICONDUCTOR LASER MODULE AND METHOD FOR FORMING
SEMICONDUCTOR LASER MODULE

AMENDMENT UNDER 37 C.F.R. § 1.111

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Commissioner for Patents
Washington, D.C. 20231

APR 16 2003

Technology Center 2600

Sir:

In response to the Office Action dated January 15, 2003, please amend the above-
identified application as follows:

IN THE CLAIMS:

Please add the following new claims:

16 (New). The semiconductor laser module of claim 2, wherein the predetermined angle
is defined as θ , and wherein

$$d = L \tan \theta,$$

where d is a depth of domain inversion and L is a length of a domain inversion region.

17 (New). The semiconductor laser module of claim 2, wherein the predetermined angle
is defined as θ , and wherein

A'

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$$d = L \tan \theta + C,$$

where d is a depth of domain inversion and L is a length of a domain inversion region,
and C is a spreading constant for domain inversion.

A' cont'd 18 (New). The semiconductor laser module of claim 16, wherein a width ratio of a
domain inversion region to a domain non-inversion region is 1:1.

19 (New). The method according to claim 12, wherein a top surface of the substrate is
disposed with a first electrode and a bottom surface of the substrate is disposed with a second
electrode, wherein the first and second electrodes are offset from each other such that the
electrodes do not overlap, said electrodes used to form the domain inversion regions.
